

B1 wherein the third width and pitch are equal to the first width and pitch, respectively;
and [The polishing pad of claim 3,]
wherein the first pitch is larger than the second pitch.

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6. (Amended) A polishing pad to polish a substrate in a chemical mechanical polishing apparatus, comprising:

B2 a first polishing region having a first plurality of substantially circular concentric grooves with a first width and a first pitch;

a second polishing region surrounding the first polishing region and having a second plurality of substantially circular concentric grooves with a second width and a second pitch;

a third polishing region surrounding the second polishing region and having a third plurality of substantially circular concentric grooves with a third width and a third pitch;

wherein at least one of the second width and second pitch differs from the first width and first pitch;

wherein the third width and pitch are equal to the first width and pitch, respectively;
and [The polishing pad of claim 3,]

wherein the first width is less than the second width.

B3 9 8
13. (Amended) The polishing pad of claim 12, wherein the first plurality of partitions cover about 75% of [the] a surface area of the first polishing region and the second plurality of partitions cover about 50% of [the] a surface area of the second polishing region.

Please add the following new claims:

14-43. (New) A polishing pad to polish a substrate in a chemical mechanical polishing apparatus, comprising:

B4 a first polishing region having a first plurality of substantially circular concentric grooves with a first width and a first pitch; and

a second polishing region surrounding the first polishing region and having a second plurality of substantially circular concentric grooves with a second width and a second pitch,
wherein the second pitch differs from the first pitch.--

15-44. (New) A polishing pad to polish a substrate in a chemical mechanical polishing apparatus, comprising:

134 a first polishing region having a first plurality of substantially circular concentric grooves with a first width and a first pitch; and

a second polishing region surrounding the first polishing region and having a second plurality of substantially circular concentric grooves with a second width and a second pitch, wherein the second width differs from the first width.--

REMARKS

Claims 4, 6 and 13 have been amended. Claims 2 and 3 have been canceled and new claims 43 and 44 have been added. No new matter has been added. Reconsideration of the rejections is respectfully requested.

Rejection Under 35 USC 112

Claim 13 was rejected under 35 USC 112 as indefinite. Claim 13 has been amended to eliminate this rejection.

Rejection Under 35 USC 102

The Examiner rejected claims 1-3, 8 and 12 under 35 USC 102(b) as anticipated by U.S. Patent No. 5,216,843 to Breivogel et al ("Breivogel"). Applicants respectfully traverses the rejection.

Claim 1 is directed to a polishing pad for polishing a substrate in a chemical mechanical polishing apparatus. The polishing pad includes a first polishing region having a first plurality of substantially circular concentric grooves with a first width and a first pitch. A second polishing region surrounds the first polishing region and has a second plurality of substantially circular concentric grooves with a second width and a second pitch, wherein at least one of the second width and second pitch differs from the first width and first pitch.

The term "width" refers to the annular width of a circular groove (e.g., the distance Wg from Figure 7 of Applicants' specification), not the diameter of the circle formed by the groove.